

AMENDMENT TO THE CLAIMS

This listing of claims replaces all prior listing of claims for this application.

Claims 1-75 (Canceled).

76. (Previously presented) A semiconductor device comprising:

a semiconductor structure having at least one metal layer formed over a surface thereof;

a first insulating layer formed over said at least one metal layer, wherein said first insulating layer is at least two microns thicker than said at least one metal layer;

at least one metal stack formed over said first insulating layer and in contact with said at least one metal layer;

a second insulating layer formed over said at least one metal stack; and,

an etched solder layer having a thickness of at least 2.33 microns, wherein said etched solder layer forms at least one solder contact in said second insulating layer and in contact with said at least one metal stack.

77. (Previously presented) The semiconductor device of claim 76, wherein said at least one solder contact has a diameter from 2 microns to 100 microns.

78. (Previously presented) The semiconductor device of claim 77, wherein said at least one solder contact has a diameter less than 50 microns.

79. (Previously presented) The semiconductor device of claim 78, wherein said at least one solder contact has a diameter less than 25 microns.

80. (Previously presented) The semiconductor device of claim 79, wherein said at least one solder contact has a diameter less than 10 microns.

81. (Previously presented) The semiconductor device of claim 79, wherein said at least one solder contact has a diameter of approximately 2 microns.

82. (Previously presented) The semiconductor device of claim 76, wherein said at least one metal stack is formed of at least three different metals.

83. (Previously presented) The semiconductor device of claim 82, wherein said three different metals are zirconium, nickel, and copper.

84. (Previously presented) The semiconductor device of claim 82, wherein said at least one metal stack comprises a fourth metal.

85. (Previously presented) The semiconductor device of claim 84, wherein said fourth metal is gold.

86. (Previously presented) The semiconductor device of claim 76, wherein said second insulating layer is approximately 1.5 microns thick.